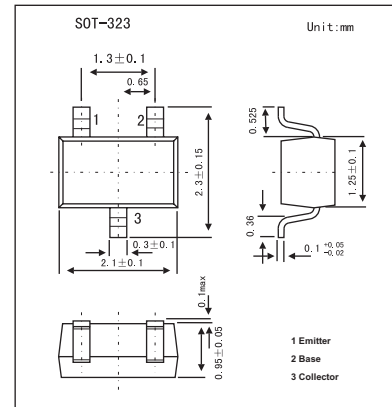


PNP Silicon Epitaxia

2SA1608

■ Features

- High fr: fr=400MHz.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-60	V
Collector-emitter voltage	V _{CEO}	-40	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-500	mA
Total power dissipation	P _T	150	mW
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	I _{CBO}	V _{CB} = -40V, I _E =0			-100	nA
Emitter cutoff current	I _{EBO}	V _{EB} = -4V, I _C =0			-100	nA
DC current gain *	h _{FE}	V _{CE} = -2V, I _C = -150mA	75	140	300	
Collector-emitter saturation voltage *	V _{CE(sat)}	I _C = -500mA, I _B = -50mA		-0.45	-0.75	V
Base-emitter saturation voltage *	V _{BE(sat)}	I _C = -500mA, I _B = -50mA		-1	-1.3	V
Gain bandwidth product	f _T	V _{CE} = -10V, I _E = 20mA	150	400		MHz
Output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1.0MHz		5	8	pF
Turn-on time	t _{on}	V _{CC} = -30V,		25		ns
Storage time	t _{stg}	I _C = 150mA,		70		ns
Turn-off time	t _{off}	I _{B1} = -I _{B2} = 15mA		100		ns

*. PW ≤ 350μs, duty cycle ≤ 2%

■ hFE Classification

Marking	Y12	Y13	Y14
hFE	75~150	100~200	150~300